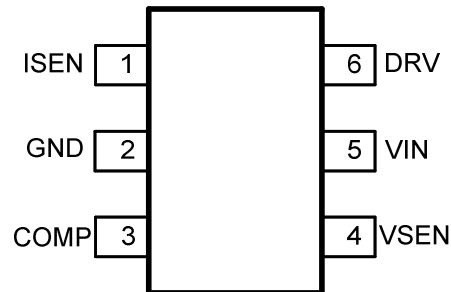




**Pinout** (top view)

**(SOT-23)**
**Top Mark: ZTxyz** (device code: **ZT**, *x*=year code, *y*=week code, *z*=lot number code)

Pin Name	Pin Number	Pin Description
ISEN	1	Current sense pin. Connect this pin to the source of the switch. Connect the sense resistor across the source of the switch and the GND pin. (current sense resistor $R_s: I_a = \frac{1}{2} \times \frac{V_{REF}}{R_s}$ ). Also this pin used to detect transformer and secondary is short or not.
GND	2	Ground pin
COMP	3	Loop compensation pin. Connect a RC network across this pin and ground to stabilize the control loop.
VSEN	4	Inductor current zero-crossing detection pin. This pin receives the auxiliary winding voltage by a resistor divider and detects the inductor current zero crossing point. This pin also provides over voltage protection and line regulation modification function simultaneously. If the voltage on this pin is above $V_{SEN,OVP}$ , the IC would enter over voltage protection mode. Good line regulation can be achieved by adjusting the upper resistor of the divider.
VIN	5	Power supply pin. This pin also provides output over voltage protection along with VSEN pin.
DRV	6	Gate drive pin. Connect this pin to the gate of MOSFET.

**Absolute Maximum Ratings** (Note 1)

VIN, DRV	-0.3V~33V
Supply Current I <sub>VIN</sub>	15mA
VSEN	-0.3V ~ V <sub>IN</sub> +0.3
ISEN, COMP	-0.3~3.6V
Power Dissipation, @ T <sub>A</sub> = 25°C SOT23-6	0.6W
Package Thermal Resistance (Note 2)	
SOT23-6, θ <sub>JA</sub>	170°C/W
SOT23-6, θ <sub>JC</sub>	130°C/W
Junction Temperature Range	-40°C to 150°C
Lead Temperature (Soldering, 10 sec.)	260°C
Storage Temperature Range	-65°C to 150°C

**Recommended Operating Conditions** (Note 3)

VIN, DRV	9.5V~27V
Junction Temperature Range	-40°C to 125°C

**Block Diagram**

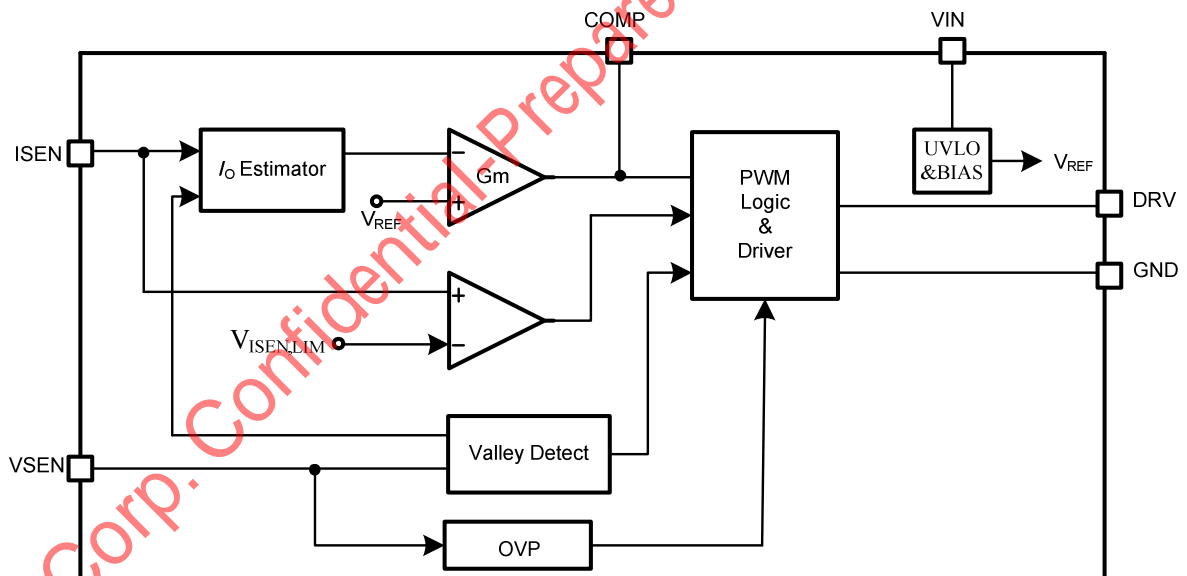


Figure3. Block Diagram

## Electrical Characteristics

( $V_{IN} = 12V$  (Note 3),  $T_A = 25^\circ C$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Power Supply Section</b>						
VIN turn-on threshold	$V_{VIN,ON}$			25.3		V
VIN turn-off threshold	$V_{VIN,OFF}$			8.5		V
VIN OVP voltage	$V_{VIN,OVP}$			30.0		V
Start up Current	$I_{ST}$	$V_{VIN} < V_{VIN,OFF}$		15		$\mu A$
Shunt current in OVP mode	$I_{VIN,OVP}$	$V_{VIN} > V_{VIN,OVP}$		4.7		mA
<b>Error Amplifier Section</b>						
Internal reference voltage	$V_{REF}$			0.3		V
<b>Current Sense Section</b>						
Current limit voltage	$V_{ISEN,LIMIT}$			0.75		V
Protection limit for TR short	$V_{ISEN,EX}$			1.5		V
CC Feedforward coefficient	$K_2$			0.1		
CC Feedforward resistor	$R_{K2}$			340		$\Omega$
<b>COMP section</b>						
Pre-charge value	$V_{COMPLIM}$			1.4		V
<b>VSEN pin Section</b>						
VSEN pin OVP voltage threshold	$V_{VSEN,OVP}$			1.5		V
Fast start up threshold	$V_{VSEN,ST}$			0.55		V
<b>Gate Driver Section</b>						
Gate driver voltage	$V_{Gate}$			11.7		V
Maximum source current	$I_{SOURCE}$			0.06		A
Minimum sink current	$I_{SINK}$			0.25		A
Max ON Time	$T_{ON,MAX}$	$V_{COMP} = 1.5V$		20		$\mu s$
Max OFF Time	$T_{OFF,MAX}$	$V_{FB} < 0.55V$		150		$\mu s$
Blanking time for ON time	$T_{ON,BLK}$			350		ns
Blanking time for OFF time	$T_{OFF,BLK}$			2		$\mu s$
Maximum switching frequency	$f_{MAX}$			113		kHz
<b>Thermal Section</b>						
Thermal Shutdown Temperature	$T_{SD}$			150		C

**Note 1:** Stresses beyond the “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**Note 2:**  $\Theta_{JA}$  is measured in the natural convection at  $T_A = 25^\circ C$  on a low effective single layer thermal conductivity test board of JEDEC 51-3 thermal measurement standard. Test condition: Device mounted on 2” x 2” FR-4 substrate PCB, 2oz copper, with minimum recommended pad on top layer and thermal vias to bottom layer ground plane.

**Note 3:** Increase VIN pin voltage gradually higher than  $V_{VIN,ON}$  voltage then turn down to 12V.

## Operation

SY5839 is a constant current Buck PFC controller targeting at LED lighting applications.

High power factor is achieved by constant on-time operation mode, with which the control scheme and the circuit structure are both simple.

Start up process is optimized inside SY5839, and quick start up (less than 500ms) is achieved without any additional circuit

In order to reduce the switching losses and improve EMI performance, Quasi-Resonant switching mode is applied, which means to turn on the power MOSFET at voltage valley; the start up current of SY5839 is rather small (15μA typically) to reduce the standby power loss further; the maximum switching frequency is clamped to 125kHz to reduce switching losses and improve EMI performance when the converter is operated at light load condition.

SY5839 provides reliable protections such as Short Circuit Protection (SCP), Open LED Protection (OLP), Over Temperature Protection (OTP), transformer shorted protection and power diode shorted protection, etc.

SY5839 is available with SOT23-6

## Applications Information

### Start up

After AC supply or DC BUS is powered on, the capacitor  $C_{VIN}$  across VIN and GND pin is charged up by BUS voltage through a start up resistor  $R_{ST}$ . Once  $V_{VIN}$  rises up to  $V_{VIN\_ON}$ , the internal blocks start to work and PWM output is enabled.

The output voltage is feedback by VSEN pin, which is taken as  $V_{FB}$ . If  $V_{FBV}$  is lower than certain threshold  $V_{VSEN\_ST}$ , which means the output voltage is not built up,  $V_{COMP}$  is pulled up to high clamped; if  $V_{FBV}$  is higher than  $V_{VSEN\_ST}$ ,  $V_{COMP}$  is under charge of the internal gain modulator.

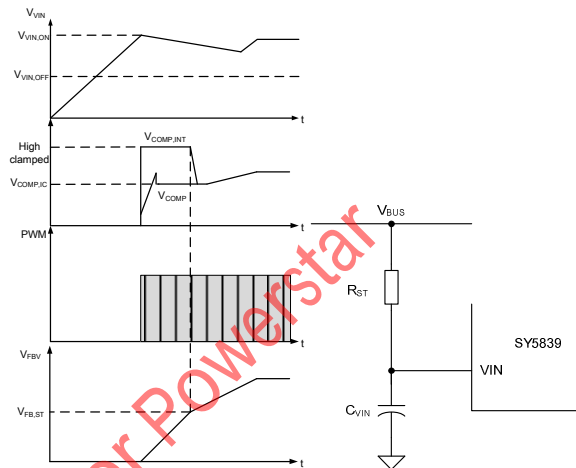


Fig. Start up

This operation is aimed to build up enough output voltage for auxiliary winding bias supply as quickly as possible. It is enabled only one time just when  $V_{VIN}$  is over  $V_{VIN\_ON}$ .

$V_{COMP}$  is pre-charged by internal current source to  $V_{COMP\_IC}$  and hold at this level until fast start up process is finished.

The start up resistor  $R_{ST}$  and  $C_{VIN}$  are designed by rules below:

(a) Preset start-up resistor  $R_{ST}$ , make sure that the current through  $R_{ST}$  is larger than  $I_{ST}$  and smaller than  $I_{VIN\_OVP}$

$$\frac{V_{BUS}}{I_{VIN\_OVP}} < R_{ST} < \frac{V_{BUS}}{I_{ST}}$$

Where  $V_{BUS}$  is the BUS line voltage.

(b) Select  $C_{VIN}$  to obtain an ideal start up time  $t_{ST}$ , and ensure the output voltage is built up at one time.

$$C_{VIN} = \frac{\left(\frac{V_{BUS}}{R_{ST}} - I_{ST}\right) \times t_{ST}}{V_{VIN\_ON}}$$

(d) If the  $C_{VIN}$  is not big enough to build up the output voltage at one time. Increase  $C_{VIN}$  and decrease  $R_{ST}$ , go back to step (a) and redo such design flow until the ideal start up procedure is obtained.

**Shut down**

After AC supply or DC BUS is powered off, the energy stored in the BUS capacitor will be discharged. When the auxiliary winding of Flyback transformer can not supply enough energy to VIN pin, V<sub>VIN</sub> will drop down. Once V<sub>VIN</sub> is below V<sub>VIN-OFF</sub>, the IC will stop working and V<sub>COMP</sub> will be discharged to zero.

**constant-current control**

The switching waveforms are shown in Fig.5. The output current I<sub>OUT</sub> can be represented by,

$$I_{OUT} = \frac{I_{PK}}{2} \times \frac{t_{EFF}}{t_s} \quad (4)$$

Where I<sub>PK</sub> is the peak current of the inductor; t<sub>EFF</sub> is the effective time of inductor current rising and falling; t<sub>s</sub> is the switching period.

I<sub>PK</sub> and t<sub>EFF</sub> can be detected by Source and VSEN pin, which is shown in Fig.6. These signals are processed and applied to the negative input of the gain modulator. In static state, the positive and negative inputs are equal.

$$V_{REF} = I_{PK} \times R_s \times \frac{t_{EFF}}{t_s} \quad (5)$$

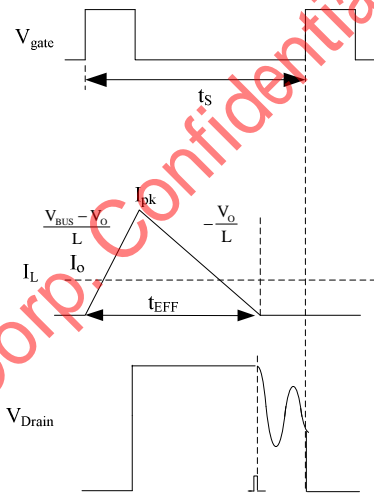


Fig.5 switching waveforms

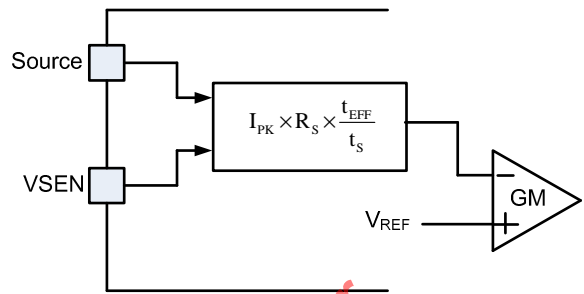


Fig.6 Output current detection diagram

Finally, the output current I<sub>OUT</sub> can be represented by

$$I_{OUT} = \frac{V_{REF}}{R_s \times 2} \quad (6)$$

Where V<sub>REF</sub> is the internal reference voltage; R<sub>s</sub> is the current sense resistor.

V<sub>REF</sub> is internal constant parameters, I<sub>OUT</sub> can be programmed by R<sub>s</sub>.

$$R_s = \frac{V_{REF}}{I_{OUT} \times 2} \quad (7)$$

**Quasi-Resonant Operation**

QR mode operation provides low turn-on switching losses for Buck converter.

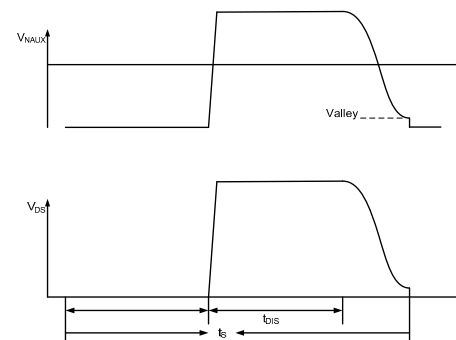


Fig.7 QR mode operation

The voltage across drain and source of the MOSFET is reflected by the auxiliary winding of the Buck transformer. VSEN pin detects the voltage across the auxiliary winding by a resistor divider. When the voltage across drain and source of the MOSFET is at voltage valley, the MOSFET would be turned on.

**Over Voltage Protection (OVP) & Open LED Protection (OLP)**

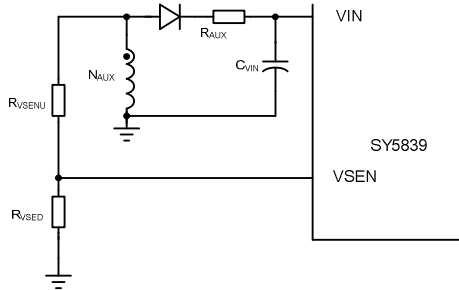


Fig. OVP&OLP

The output voltage is reflected by the auxiliary winding voltage of the Flyback transformer, and both VSEN pin and VIN pin provide over voltage protection function. When the load is null or large transient happens, the output voltage will exceed the rated value. When  $V_{VIN}$  exceeds  $V_{VIN\_OVP}$  or  $V_{VSEN}$  exceeds  $V_{VSEN\_OVP}$ , the over voltage protection is triggered and the IC will discharge  $V_{VIN}$  by an internal current source  $I_{VIN\_OVP}$ . Once  $V_{VIN}$  is below  $V_{VIN\_OFF}$ , the IC will shut down and be charged again by BUS voltage through start up resistor. If the over voltage condition still exists, the system will operate in hiccup mode.

Thus, the turns of the auxiliary winding  $N_{AUX}$  and the resistor divider is related with the OVP function.

$$\frac{V_{SEN\_OVP}}{V_{OVP}} = \frac{R_{VSEND}}{R_{VSENU} + R_{VSEND}}$$

$$\frac{V_{VIN\_OVP}}{V_{OVP}} \geq \frac{N_{AUX}}{N_S}$$

Where  $V_{OVP}$  is the output over voltage specification;  $R_{VSENU}$  and  $R_{VSEND}$  compose the resistor divider. The turns ratio of  $N_S$  to  $N_{AUX}$  and the ratio of  $R_{VSENU}$  to  $R_{VSEND}$  could be induced from equation above.

**Short Circuit Protection (SCP)**

When the output is shorted to ground, the output voltage is clamped to zero. The voltage of the auxiliary winding is proportional to the output winding, so valley signal cannot be detected by VSEN. Without valley detection, MOSFET cannot be turned ON until maximum off time  $t_{OFF\_MAX}$  is matched. If MOSFET is turned ON by  $t_{OFF\_MAX}$

64 times continuously, IC will be shut down and enter into hiccup mode.

If the output voltage is not low enough to disable valley detection in short condition,  $V_{VIN}$  will drop down without auxiliary winding supply. Once  $V_{VIN}$  is below  $V_{VIN\_OFF}$ , the IC will shut down and be charged again by the BUS voltage through the start up resistor. If the short circuit condition still exists, the system will operate in hiccup mode.

**Line regulation modification**

The IC provides line regulation modification function to improve line regulation performance.

Due to the sample delay of ISEN pin and other internal delay, the output current increases with increasing input BUS line voltage. A small compensation voltage  $\Delta V_{ISEN\_C}$  is added to ISEN pin during ON time to improve such performance. This  $\Delta V_{ISEN\_C}$  is adjusted by the upper resistor of the divider connected to VSEN pin.

$$\Delta V_{ISEN\_C} = (V_{BUS} - V_{OUT}) \times \frac{N_{AUX}}{N} \times \frac{1}{R_{VSENU}} \times K_2 \times (R_{K2} + R_{ISEN\_C})$$

Where  $R_{VSENU}$  is the upper resistor of the divider;  $k_2$  is an internal constant as the modification coefficient;  $R_{K2}$  is an internal feed-forward resistor; auxiliary resistor  $R_{ISEN\_C}$  can be added to enhance feed-forward effects.

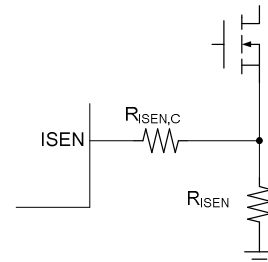


Fig. feed-forward resistor

**Power Device Design**

**MOSFET and Diode**

When the operation condition is with maximum input voltage and full load, the voltage stress of MOSFET and output power diode is maximized;

$$V_{MOS\_DS\_MAX} = \sqrt{2}V_{AC\_MAX} \quad (13)$$

$$V_{D,R\_MAX} = \sqrt{2}V_{AC\_MAX} \quad (14)$$

Where  $V_{AC\_MAX}$  is maximum input AC RMS voltage.

When the operation condition is with minimum input voltage and full load, the current stress of MOSFET and power diode is maximized.

**Inductor (L)**

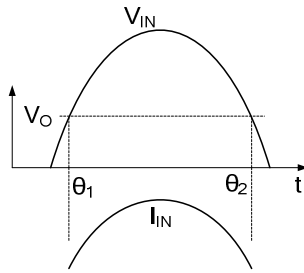


Fig.9 input waveforms

The power is transferred from AC input to output only when the input voltage is larger than output voltage in Buck converter. The input voltage and inductor current waveforms are shown in Fig.9, where  $\theta_1$  and  $\theta_2$  are the time that input voltage is equal to output voltage.

In Quasi-Resonant mode, each switching period cycle  $t_S$  consists of three parts: current rising time  $t_1$ , current falling time  $t_2$  and quasi-resonant time  $t_3$ , shown in Fig.10.

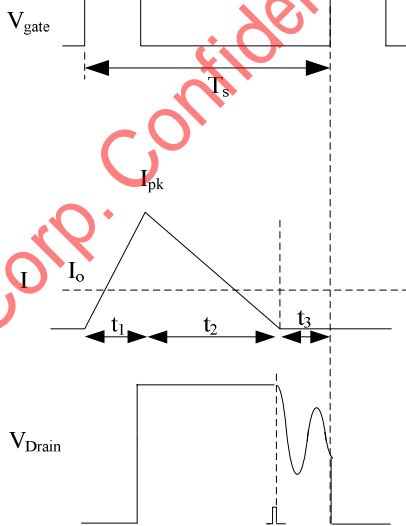


Fig.10 switching waveforms

The system operates in the constant on time mode to achieve high power factor. The ON time increases with the input AC RMS voltage decreasing and the load

increasing. When the operation condition is with minimum input AC RMS voltage and full load, the ON time is maximized. On the other hand, when the input voltage is at the peak value, the OFF time is maximized. Thus, the minimum switching frequency  $f_{S\_MIN}$  happens at the peak value of input voltage with minimum input AC RMS voltage and maximum load condition; Meanwhile, the maximum peak current through MOSFET and the transformer happens.

Once the minimum frequency  $f_{S\_MIN}$  is set, the inductance of the transformer could be Calculated. The design flow is shown as below:

(a) Preset minimum frequency  $f_{S\_MIN}$

(b) Compute relative  $t_s, t_1$

$$t_s = \frac{1}{f_{S\_MIN}} \quad (15)$$

$$t_1 = \frac{t_s \times (V_{OUT} + V_{DF})}{(\sqrt{2}V_{AC\_MIN} + V_{DF})} \quad (16)$$

$$t_2 = t_s - t_1 \quad (17)$$

Where  $V_{DF}$  is the forward voltage of the diode

(c) Design inductance L

$$\theta_1 = \arcsin\left(\frac{V_{OUT}}{\sqrt{2}V_{AC\_MIN}}\right) \times \frac{1}{\pi} \times \frac{1}{2 \times f_{AC}} \quad (18)$$

$$\theta_2 = \frac{1}{2 \times f_{AC}} - \theta_1 \quad (19)$$

$$L = \frac{\eta \times f_{AC} \times V_{OUT} \times t_1 \times P_{OUT}}{[\sqrt{2}V_{AC\_MIN} \times \frac{\cos(2\pi f_{AC} \times \theta_1) - \cos(2\pi f_{AC} \times \theta_2)}{2\pi f_{AC}} - V_{OUT}(\theta_2 - \theta_1)]} \quad (20)$$

Where  $\eta$  is the efficiency;  $P_{OUT}$  is rated full load power ;

(d) compute inductor maximum peak current  $I_{L\_PK\_MAX}$ .

$$I_{L\_PK\_MAX} = \frac{(\sqrt{2}V_{AC\_MIN} - V_{OUT}) \times t_1}{L} \quad (21)$$

Where  $I_{L\_PK\_MAX}$  is maximum inductor peak current ;

(e) compute RMS current of the inductor

$I_{L\_RMS\_MAX}$  is Inductor RMS current of whole AC period



$$I_{L\_RMS\_MAX} = \frac{t_1}{\sqrt{3} \times L} \sqrt{V_{AC\_MIN}^2 + V_{OUT}^2} - \frac{4\sqrt{2}V_{AC\_MIN} \times V_{OUT}}{\pi}$$

(22)

(f) compute RMS current of the MOSFET

$$I_{L\_RMS\_MAX} = \sqrt{\frac{t_1}{3t_s}} \times \frac{t_1}{L} \sqrt{V_{AC\_MIN}^2 + V_{OUT}^2} - \frac{4\sqrt{2}V_{AC\_MIN} \times V_{OUT}}{\pi}$$

(23)

### Inductor design (N, N<sub>AUX</sub>)

the parameters below are necessary:

Necessary parameters	
Inductance	L
inductor maximum current	I <sub>L-PK-MAX</sub>
inductor maximum RMS current	I <sub>L-RMS-MAX</sub>

The design rules are as followed:

(a) Select the magnetic core style, identify the effective area A<sub>e</sub>.

(b) Preset the maximum magnetic flux ΔB

$$\Delta B = 0.22 \sim 0.26T$$

(c) Compute primary turn N

$$N = \frac{L_M \times I_{L\_PK\_MAX}}{\Delta B \times A_e} \quad (24)$$

(d) compute auxiliary turn N<sub>AUX</sub>

$$N_{AUX} = N \times \frac{V_{MIN}}{V_{OUT}} \quad (25)$$

Where V<sub>VIN</sub> is the working voltage of VIN pin (10V~11V is recommended).

(e) Select an appropriate wire diameter with I<sub>L-RMS-MAX</sub>, select appropriate wire to make sure the current density ranges from 4A/mm<sup>2</sup> to 10A/mm<sup>2</sup>.

(f) If the winding area of the core and bobbin is not enough, reselect the core style, go to (a) and redesign the transformer until the ideal transformer is achieved.

### Output capacitor C<sub>OUT</sub>

Preset the output current ripple ΔI<sub>OUT</sub>, C<sub>OUT</sub> is induced by

$$C_{OUT} = \frac{\sqrt{\left(\frac{2I_{OUT}}{\Delta I_{OUT}}\right)^2 - 1}}{4\pi f_{AC} R_{LED}} \quad (26)$$

Where I<sub>OUT</sub> is the rated output current; ΔI<sub>OUT</sub> is the demanded current ripple; f<sub>AC</sub> is the input AC supply frequency; R<sub>LED</sub> is the equivalent series resistor of the LED load.

### Single fault design

If VSEN pin is shorted to GND pin or floating, valley detection is failed, which is similar to SLP, the system will operate in hiccup mode.

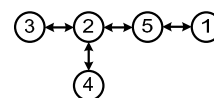
If the transformer is shorted, V<sub>ISEN</sub> will exceeds V<sub>ISEN,EX</sub>, which will trigger IC latch operation. In latch mode, IC won't work unless AC source restarts. The protection above is also suitable for secondary diode short.

### Layout

(a) To achieve better EMI performance and reduce line frequency ripples, the output of the bridge rectifier should be connected to the BUS line capacitor first, then to the switching circuit.

(b) The circuit loop of all switching circuit should be kept small.

(c) The connection of ground is recommended as:



Ground ①: ground of BUS line capacitor

Ground ②: ground of bias supply capacitor and GND pin

Ground ③: ground node of auxiliary winding

Ground ④: ground of signal trace except GND pin

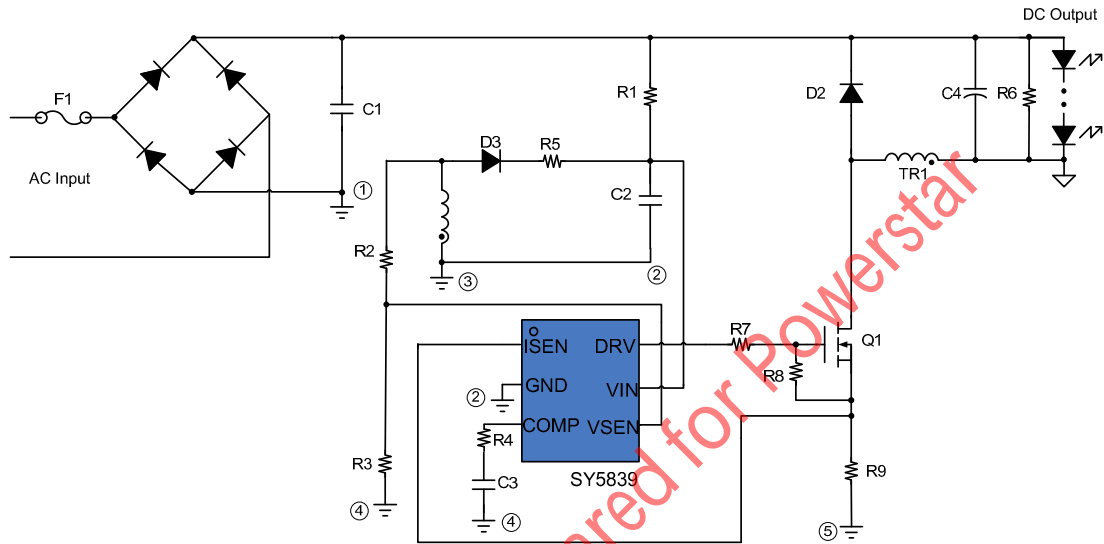
Ground ⑤: ground node of current sample resistor.

(d) bias supply trace should be connected to the bias supply capacitor first instead of GND pin. The bias supply capacitor should be put beside the IC.

(e) Loop of 'Source pin – current sample resistor – GND pin' should be kept as small as possible.

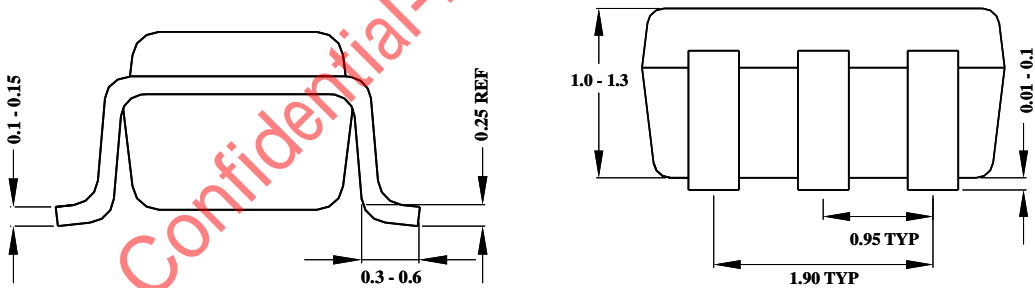
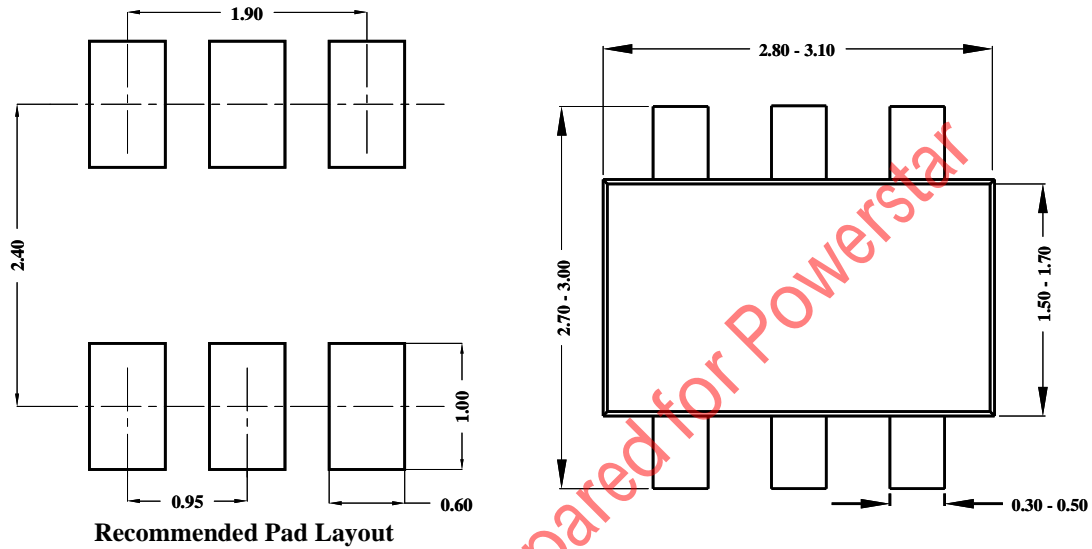
(f) The resistor divider connected to VSEN pin is recommended to be put beside the IC.

(g) The control circuit is recommended to be put outside the power circuit loop.



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SOT23-6 Package outline & PCB layout design

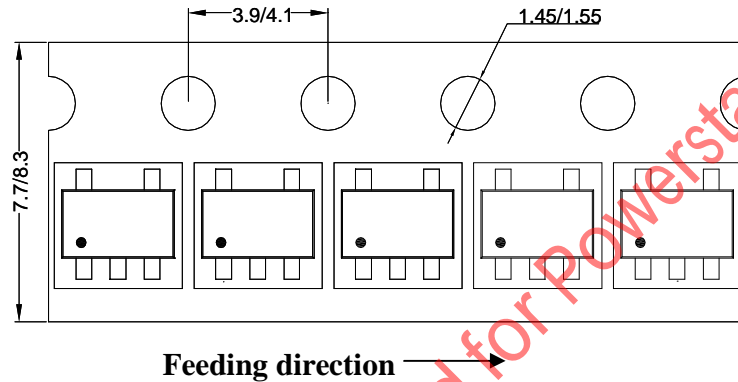


**Notes:** All dimensions are in millimeters.  
All dimensions don't include mold flash & metal burr.

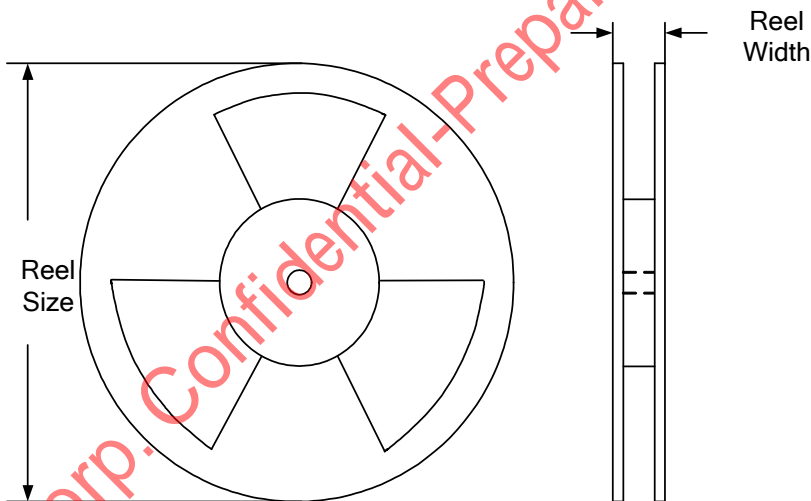
## Taping & Reel Specification

### 1. Taping orientation

SOT23-6



### 2. Carrier Tape & Reel specification for packages



Package types	Tape width (mm)	Pocket pitch(mm)	Reel size (Inch)	Reel width(mm)	Trailer length(mm)	Leader length (mm)	Qty per reel
SOT23-6	8	4	7"	8.4	280	160	3000

### 3. Others: NA

单击下面可查看定价，库存，交付和生命周期等信息

[>>SILERGY\(矽力杰\)](#)